

SANYO Semiconductors

DATA SHEET



NPN Epitaxial Planar Silicon Transistor **2SC3950** — High-Definition CRT Display **Video Output Applications**

Applications

· High-definition CRT display video output, wide-band amplifier.

Features

- High f_T : $f_T=2.0GHz$.
- Large current capacity : IC=500mA.
- · Micaless type : TO-126 plastic package.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		30	V
Collector-to-Emitter Voltage	VCEO		20	V
Emitter-to-Base Voltage	VEBO		3	V
Collector Current	IC		500	mA
Collector Current (Pulse)	ICP		1000	mA
Collector Dissipation	PC		1.3	W
		Tc=25°C	5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =20V, I _E =0A			0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =2V, I _C =0A			5.0	μΑ

Continued on next page.

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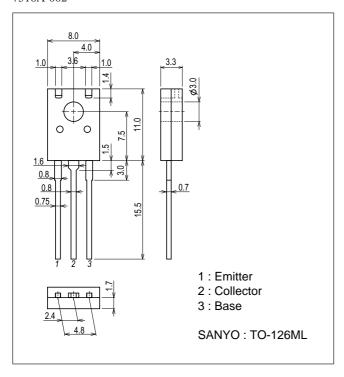
Parameter	Symbol	Conditions	Ratings			Unit	
Falameter	Symbol	Conditions	min	typ	max	Unit	
DC Current Gain	hFE1	VCE=5V, IC=50mA	40*		200*		
	hFE2	V _{CE} =5V, I _C =500mA	20				
Gain-Bandwidth Product	fΤ	V _{CE} =5V, I _C =100mA		2.0		GHz	
Output Capacitance	Cob	VCB=10V, f=1MHz		6.0		pF	
Reverse Transfer Capacitance	Cre	V _{CB} =10V, f=1MHz		4.6		pF	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=300mA, IB=30mA		0.3	0.8	V	
Base-to-Emitter Saturation Voltage VBE(sat) IC=300mA,		IC=300mA, IB=30mA		0.9	1.2	V	

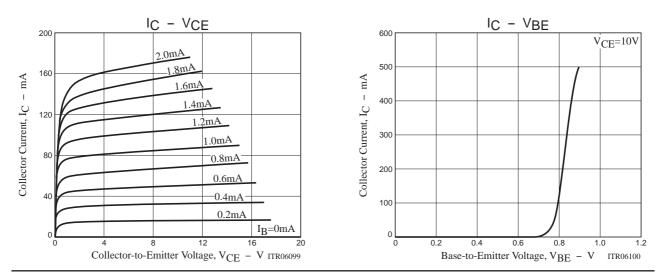
 $^{*}h_{FE}1$: The 2SC3950 is classified by 50mA h_{FE} as follows :

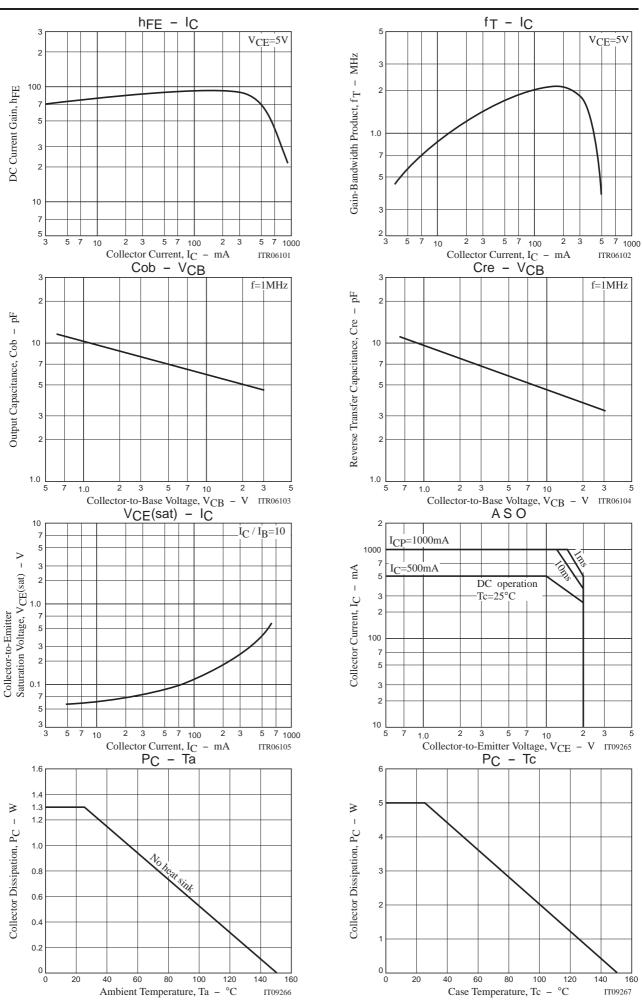
Rank	С	D	Е
hFE	40 to 80	60 to 120	100 to 200

Package Dimensions

unit : mm (typ) 7516A-002







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